

# Chi-Feng Li

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/2881477/publications.pdf>

Version: 2024-02-01

4  
papers

34  
citations

2682572

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2917675

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4  
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times ranked

85  
citing authors

#	ARTICLE	IF	CITATIONS
1	First demonstration of 40-nm channel length top-gate WS <sub>2</sub> pFET using channel area-selective CVD growth directly on SiO <sub>x</sub> /Si substrate. , 2019, , .		22
2	Experimentally Determining the Top and Edge Contact Resistivities of Two-Step Sulfurization Nb-Doped MoS <sub>2</sub> Films Using the Transmission Line Measurement. IEEE Electron Device Letters, 2019, 40, 1662-1665.	3.9	7
3	Demonstration of 40-nm Channel Length Top-Gate p-MOSFET of WS <sub>2</sub> Channel Directly Grown on SiO <sub>x</sub> /Si Substrates Using Area-Selective CVD Technology. IEEE Transactions on Electron Devices, 2019, 66, 5381-5386.	3.0	5
4	Comparison of Experimentally Extracted Top and Edge Contact Resistivity by TLM Structure with Two-step Sulfurization Nb-Doped MoS <sub>2</sub> . , 2019, , .		0